

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

h_{FE}
Excellent h_{FE} linearity, low $V_{CE(sat)}$, high P_C .

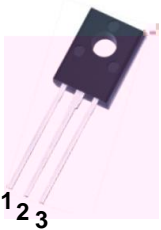
/ Applications

Audio frequency amplifier and switching, especially in hybrid integrated circuits applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

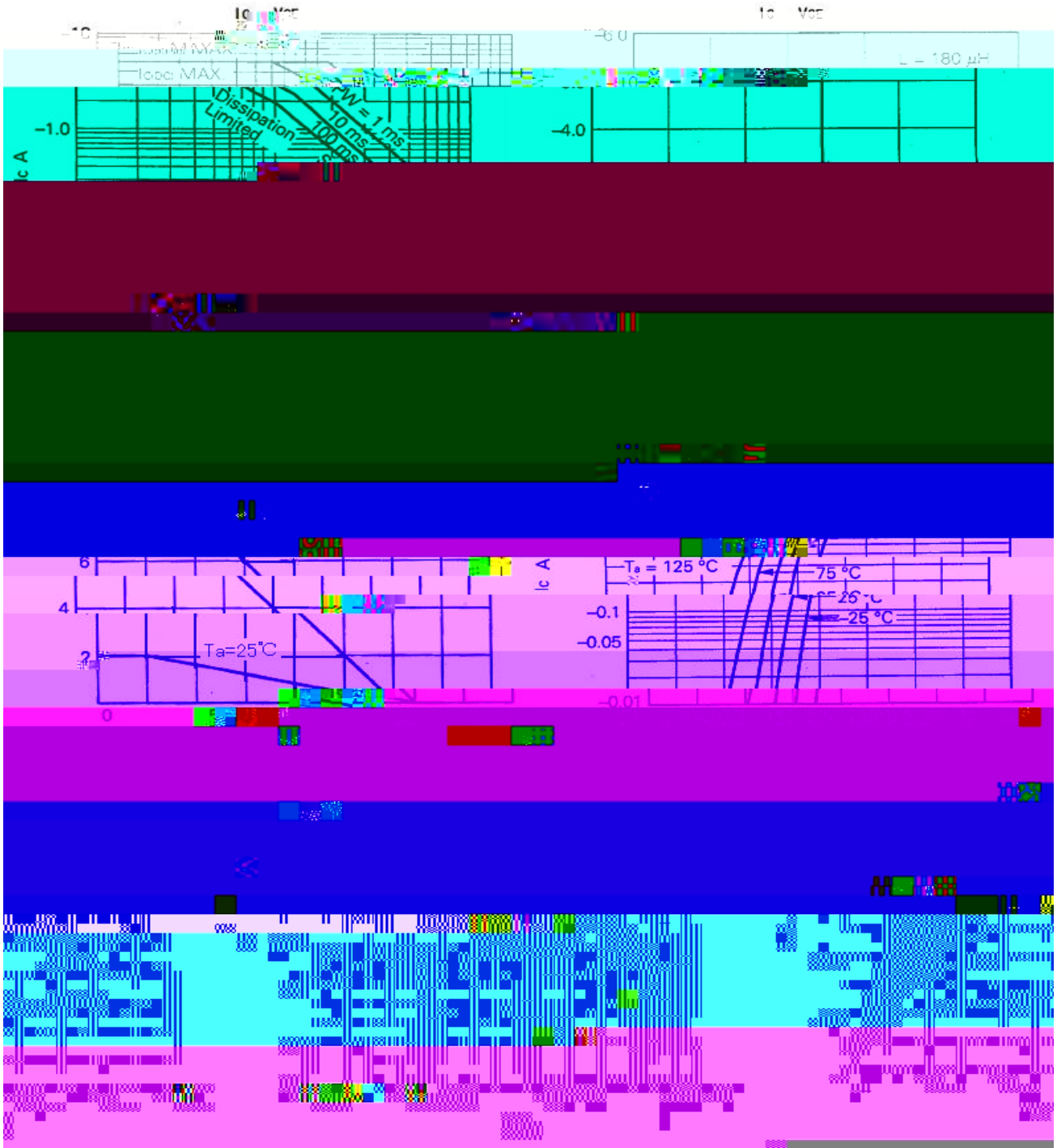
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_C=125^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-0.1mA$ $I_E=0$	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-0.1mA$ $I_C=0$	-7.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V$ $I_E=0$			-10	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-7.0V$ $I_C=0$			-10	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0V$ $I_C=-600mA$	100		400	
	$h_{FE(2)}$	$V_{CE}=-2.0V$ $I_C=-200mA$	60			
	$h_{FE(3)}$	$V_{CE}=-2.0V$ $I_C=-2.0A$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A$ $I_B=-150mA$			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-1.5A$ $I_B=-150mA$			-1.2	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_C=-1.5A$		50		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$		40		pF

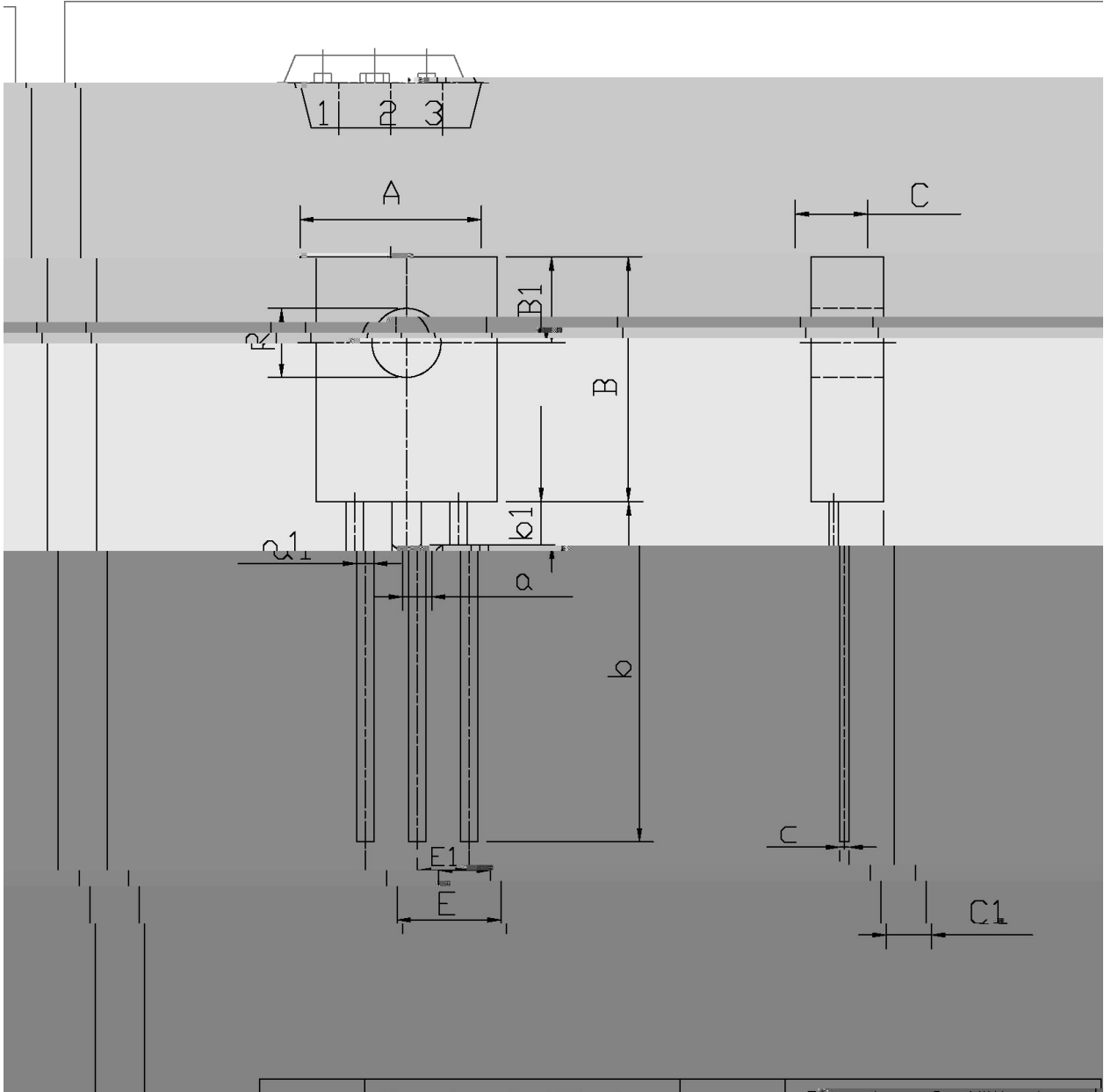
/ Electrical Characteristic Curve



/ Package Dimensions

2SB1261L

单位: mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	A1	0.66	0.86

/ Marking Instructions



BR

B1261

M:

h_{FE}

2SB1261L
Rev.E Mar.-2016

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